Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-12. Cancelled.

13. (Previously Presented) A method for manufacturing a semiconductor device, comprising:

forming a lower dielectric layer on top of a lower metal layer;

forming an upper metal layer on top of the lower dielectric layer;

forming an upper dielectric layer on top of the upper metal layer;

forming a cavity that extends through the upper dielectric layer, the upper metal layer and the lower dielectric layer, and that serves as a contact region for access to a solder pad portion of the lower metal layer;

forming a dielectric lining layer on the upper dielectric layer such that the dielectric lining layer fills the cavity;

removing a central portion of the dielectric lining layer from the cavity such that the dielectric lining lines a peripheral cavity-confining surface of the cavity that is transverse to a plane of the lower metal layer to isolate the upper metal layer form the lower metal layer while permitting access to the solder pad portion of the lower metal layer; and

filling the cavity with a liquid metal to form an electrical contact that enables external electrical connection with the lower metal layer.

14. (Previously Presented) The method of Claim 13, further comprising the step of forming a grounding trace that is disposed on the upper dielectric layer and that is disposed on the upper dielectric layer and that surrounds the cavity prior to forming the

dielectric lining layer, the dielectric lining layer being subsequently formed to extend on top of the upper dielectric layer to conceal the grounding trace.

15. (Previously Presented) The method of Claim 13, wherein the liquid metal is a conductive metal paste.

16. (Previously Presented) The method of Claim 13, wherein the dielectric lining layer is made of a photoresist material, and the step of removing the central portion of the dielectric lining layer from the cavity includes:

superimposing a patterned mask on the dielectric lining layer; and

exposing and developing the dielectric lining layer.